



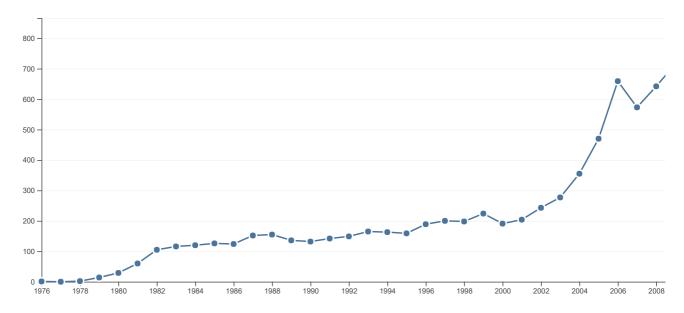
Sum of Times Cited 6
12,905
9,744

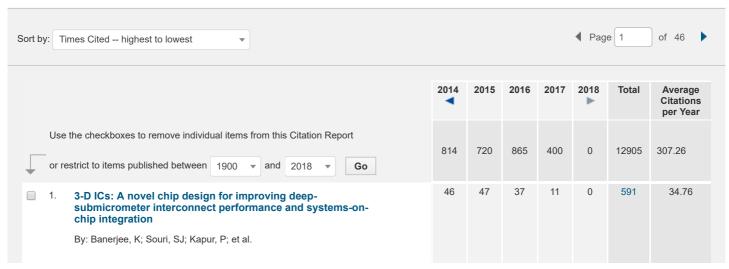
Without self citations 6
12,244
9,474

Export Data:

Save to Text File

Sum of Times Cited per Year





9/7/2017	Web of Science [v.5.25.1] - Web of Science C	ore Coll	ection (Citation	Report			
	PROCEEDINGS OF THE IEEE Volume: 89 Issue: 5 Special Issue: SI Pages: 602-633 Published: MAY 2001							
_ 2.	Nanometre-scale germanium photodetector enhanced by a near-infrared dipole antenna							
	By: Tang, Liang; Kocabas, Sukru Ekin; Latif, Salman; et al. NATURE PHOTONICS Volume: 2 Issue: 4 Pages: 226-229 Published: APR 2008	56	41	51	25	0	395	39.50
3.	Germanium nanowire field-effect transistors with SiO2 and high-kappa HfO2 gate dielectrics							
	By: Wang, DW; Wang, Q; Javey, A; et al. APPLIED PHYSICS LETTERS Volume: 83 Issue: 12 Pages: 2432-2434 Published: SEP 22 2003	17	14	22	9	0	345	23.00
_ 4.	A Sub-400 degrees C germanium MOSFET technology with high-kappa dielectric and metal gate							
	By: Chui, CO; Kim, H; Chi, D; et al. Book Group Author(s): ELECTRONIC DEVICES SOCIETY OF IEEE; ELECTRONIC DEVICES SOCIETY OF IEEE Conference: IEEE International Electron Devices Meeting Location: SAN FRANCISCO, CA Date: DEC 08-11, 2002 Sponsor(s): IEEE Elect Devices Soc INTERNATIONAL ELECTRON DEVICES 2002 MEETING, TECHNICAL DIGEST Pages: 437-440 Published: 2002	8	10	7	4	0	302	18.88
<u> </u>	DOPANT SEGREGATION IN POLYCRYSTALLINE SILICON							
	By: MANDURAH, MM; SARASWAT, KC; HELMS, CR; et al. JOURNAL OF APPLIED PHYSICS Volume: 51 Issue: 11 Pages: 5755- 5763 Published: 1980	5	7	3	3	0	298	7.84
<u> </u>	Interconnect limits on gigascale integration (GSI) in the 21st century							
	By: Davis, JA; Venkatesan, R; Kaloyeros, A; et al. PROCEEDINGS OF THE IEEE Volume: 89 Issue: 3 Special Issue: SI Pages: 305-324 Published: MAR 2001	8	9	12	5	0	276	16.24
7 .	TWO-DIMENSIONAL THERMAL-OXIDATION OF SILICON .2. MODELING STRESS EFFECTS IN WET OXIDES							
	By: KAO, DB; MCVITTIE, JP; NIX, WD; et al. IEEE TRANSACTIONS ON ELECTRON DEVICES Volume: 35 Issue: 1 Pages: 25-37 Published: JAN 1988	8	6	8	4	0	275	9.17
8.	Germanium MOS capacitors incorporating ultrathin high-kappa gate dielectric							
	By: Chui, CO; Ramanathan, S; Triplett, BB; et al. IEEE ELECTRON DEVICE LETTERS Volume: 23 Issue: 8 Pages: 473-475 Published: AUG 2002	10	9	13	3	0	273	17.06
9.	Activation and diffusion studies of ion-implanted p and n dopants in germanium							
	By: Chui, CO; Gopalakrishnan, K; Griffin, PB; et al. APPLIED PHYSICS LETTERS Volume: 83 Issue: 16 Pages: 3275-3277 Published: OCT 20 2003	20	11	14	3	0	201	13.40
_ 10	TWO-DIMENSIONAL THERMAL-OXIDATION OF SILICON .1. EXPERIMENTS							
	By: KAO, DB; MCVITTIE, JP; NIX, WD; et al. IEEE TRANSACTIONS ON ELECTRON DEVICES Volume: 34 Issue: 5 Pages: 1008-1017 Published: MAY 1987	6	3	6	3	0	194	6.26
☐ Sel	ect Page Save to Text File							
Sort by: Times Cited highest to lowest ▼								
Sort by: Times Cited highest to lowest								
455 reco	rds matched your query of the 65,301,887 in the data limits you selected.							

© 2017 CLARIVATE ANALYTICS TERMS OF USE PRIVACY POLICY FEEDBACK